# CHIP MONOLITHIC CERAMIC CAPACITOR

## High-power Type GRM600 Series

#### Features

- 1. Mobile Telecommunication and RF module, mainly.
- 2. Quality improvement of telephone call, Low power Consumption, yield ratio improvement.

#### Application

VCO, PA, Mobile Telecommunication



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Dort Number	Dimensions (mm)							
Part Number	L	W	Т	е	g min.			
GRM615	1.0 ±0.05	0.5 ±0.05	0.5 ±0.05	0.15 to 0.3	0.4			

Part Number	Rated Voltage (Vdc)	TC Code	Capacitance (pF)	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM615C0G010B50	50	C0G	1.0 –0.1pF	1.00	0.50	0.50
GRM615C0G010C50	50	C0G	1.0 –0.25pF	1.00	0.50	0.50
GRM615C0G020B50	50	C0G	2.0 –0.1pF	1.00	0.50	0.50
GRM615C0G020C50	50	COG	2.0 –0.25pF	1.00	0.50	0.50
GRM615C0G030B50	50	COG	3.0 –0.1pF	1.00	0.50	0.50
GRM615C0G030C50	50	C0G	3.0 –0.25pF	1.00	0.50	0.50
GRM615C0G040B50	50	C0G	4.0 –0.1pF	1.00	0.50	0.50
GRM615C0G040C50	50	C0G	4.0 –0.25pF	1.00	0.50	0.50
GRM615C0G050B50	50	C0G	5.0 –0.1pF	1.00	0.50	0.50
GRM615C0G050C50	50	C0G	5.0 –0.25pF	1.00	0.50	0.50
GRM615C0G060C50	50	COG	6.0 –0.25pF	1.00	0.50	0.50
GRM615C0G060D50	50	C0G	6.0 –0.5pF	1.00	0.50	0.50
GRM615C0G070C50	50	C0G	7.0 –0.25pF	1.00	0.50	0.50
GRM615C0G070D50	50	C0G	7.0 –0.5pF	1.00	0.50	0.50
GRM615C0G080C50	50	C0G	8.0 –0.25pF	1.00	0.50	0.50
GRM615C0G080D50	50	C0G	8.0 –0.5pF	1.00	0.50	0.50
GRM615C0G090C50	50	C0G	9.0 –0.25pF	1.00	0.50	0.50
GRM615C0G090D50	50	C0G	9.0 –0.5pF	1.00	0.50	0.50
GRM615C0G0R5B50	50	C0G	0.5 –0.1pF	1.00	0.50	0.50
GRM615C0G0R5C50	50	C0G	0.50 –0.25pF	1.00	0.50	0.50
GRM615C0G100C50	50	C0G	10 –0.25pF	1.00	0.50	0.50
GRM615C0G100D50	50	C0G	10.0 –0.5pF	1.00	0.50	0.50
GRM615C0G110G50	50	C0G	11 –2%	1.00	0.50	0.50
GRM615C0G120G50	50	COG	12 –2%	1.00	0.50	0.50
GRM615C0G120J50	50	C0G	12 –5%	1.00	0.50	0.50
GRM615C0G130G50	50	COG	13 –2%	1.00	0.50	0.50
GRM615C0G150G50	50	COG	15 –2%	1.00	0.50	0.50
GRM615C0G150J50	50	COG	15 –5%	1.00	0.50	0.50
GRM615C0G160G50	50	COG	16 –2%	1.00	0.50	0.50
GRM615C0G180G50	50	C0G	18 –2%	1.00	0.50	0.50
GRM615C0G180J50	50	COG	18 –5%	1.00	0.50	0.50
GRM615C0G1R1B50	50	COG	1.1 –0.1pF	1.00	0.50	0.50
GRM615C0G1R2B50	50	COG	1.2 –0.1pF	1.00	0.50	0.50
GRM615C0G1R3B50	50	COG	1.3 –0.1pF	1.00	0.50	0.50
GRM615C0G1R5B50	50	COG	1.5 –0.1pF	1.00	0.50	0.50
GRM615C0G1R5C50	50	COG	1.5 –0.25pF	1.00	0.50	0.50
GRM615C0G1R6B50	50	COG	1.6 –0.1pF	1.00	0.50	0.50
GRM615C0G1R8B50	50	COG	1 8 –0 1pF	1.00	0.50	0.50

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Part Number	Rated Voltage (Vdc)	TC Code	Capacitance (pF)	Length L (mm)	Width W (mm)	Thickness T (mm)
GRM615C0G200G50	50	C0G	20 –2%	1.00	0.50	0.50
GRM615C0G2R2B50	50	C0G	2.2 –0.1pF	1.00	0.50	0.50
GRM615C0G2R4B50	50	C0G	2.4 –0.1pF	1.00	0.50	0.50
GRM615C0G2R7B50	50	C0G	2.7 –0.1pF	1.00	0.50	0.50
GRM615C0G3R3B50	50	C0G	3.3 –0.1pF	1.00	0.50	0.50
GRM615C0G3R6B50	50	C0G	3.6 –0.1pF	1.00	0.50	0.50
GRM615C0G3R9B50	50	C0G	3.9 –0.1pF	1.00	0.50	0.50
GRM615C0G4R3B50	50	C0G	4.3 –0.1pF	1.00	0.50	0.50
GRM615C0G4R7B50	50	C0G	4.7 –0.1pF	1.00	0.50	0.50
GRM615C0G5R1C50	50	C0G	5.1 –0.25pF	1.00	0.50	0.50
GRM615C0G5R6C50	50	C0G	5.6 –0.25pF	1.00	0.50	0.50
GRM615C0G6R2C50	50	C0G	6.2 –0.25pF	1.00	0.50	0.50
GRM615C0G6R8C50	50	C0G	6.8 –0.25pF	1.00	0.50	0.50
GRM615C0G7R5C50	50	C0G	7.5 –0.25pF	1.00	0.50	0.50
GRM615C0G8R2C50	50	C0G	8.2 –0.25pF	1.00	0.50	0.50
GRM615C0G9R1C50	50	COG	9.1 –0.25pF	1.00	0.50	0.50



## Specifications and Test Methods

			Specification											
No.	lte	em	Temperature Compensating Type	Test Method										
1	1 Operating Temperature Range		−55 to +125℃											
2	2 Rated Voltage		See the previous pages.	The rated voltage is defined as the maximum voltage which may be applied continuously to the capacitor. When AC voltage is superimposed on DC voltage, V <sup>p.p</sup> or V <sup>0.p</sup> , whichever is larger, shall be maintained within the rated voltage range.										
3	Appeara	nce	No defects or abnormalities.	Visual inspection.										
4	Dimensio	ons	Within the specified dimensions.	Using calipers.										
5	Dielectric	: Strength	No defects or abnormalities.	No failure shall be observed when 300% of the applied between the terminations for 1 to 5 set the charge/discharge current is less than 50m.	e rated voltage is conds, provided A.									
6	Insulation (I.R.)	Resistance	10,000M $\Omega$ min. or 500 $\Omega$ • F min. (Whichever is smaller)	The insulation resistance shall be measured w not exceeding the rated voltage at 25°C and 75 within 2 minutes of charging.	vith a DC voltage 5%RH max. and									
7	Capacita	nce	Within the specified tolerance.	The capacitance/Q shall be measured at $25^{\circ}$ C	at the frequency									
				and voltage shown in the table.										
8	0		30pF min. : Q≧1,000 30pF max : Q≥400+20C	Item Char. COG(1000pF and	d below)									
0	2		C : Nominal Capacitance (pF)		12 n.c									
				0.5 to 5 v1.1	11.5.									
	Capaci		Within the specified tolerance. (Table A-1)	The capacitance change shall be measured af	fter 5 min. at									
		Change		each specified temperature stage.										
		Temperature	Within the specified tolerance. (Table A-1)	The temperature coefficient is determined usin	ng the									
		Coefficent		capacitance measured in step 3 as a reference	e.									
9	Capacitance Temperature Characteristics	S Capacitance Drift	Canacitance	acitance perature acteristics Capacitance Within ±0.2%	Within ±0.2% or ±0.05pF	When cycling the temperature sequentially from 5, (COG : $+25^{\circ}$ to $+125^{\circ}$ : other temp. coeffs, the capacitance shall be within the specified to temperature coefficient and capacitance change. The capacitance drift is calculated by dividing between the maximum and minimum measure step 1, 3 and 5 by the cap value in step 3.	m step 1 through $.: +25^{\circ}$ to $85^{\circ}$ ) olerance for the ge as Table A. the differences ad values in the							
			(Whichever is larger.)	Step Temperature(	(°°)									
					1 25±2									
													2 -55±3	
					<u>3</u> 25±2									
				4 125±3										
				5 25±2										
10	10 Adhesive Strength		No removal of the terminations or other defect shall occur.	Solder the capacitor to the test jig (glass epoxy b Fig.1 using a eutectic solder. Then apply a 5N for with the test jig for 10 $\pm$ 1sec. The soldering shall be done either with an iron of method and shall be conducted with care so that uniform and free of defects such as heat shock.	board) shown in orce in parallel or using the reflow at the soldering is									
	of Termir	nation												
				Type a b	С									
				GRM615 0.4 1.5	0.5									
				(in mm) Fig.1										

Continued on the following page.



### Specifications and Test Methods

#### Continued from the preceding page.

			Specification								
No.	Ite	em	Tem	perature Com	pensating Ty	уре	-	Tes	t Method	ł	
		Appearance	No defects or abno	ormalities.			Solder the capacitor to the test jig (glass epoxy board) in the				
		Capacitance	<ul> <li>Within the specified tolerance.</li> <li>30pF min. : Q≥1,000</li> <li>30pF max. : Q≥400+20C</li> <li>C : Nominal Capacitance (pF)</li> </ul>				same manner	and under the	same co	nditions as (10)	).
11	Vibration Resistance	Q					I he capacitor shall be subjected to a simple harmonic motion having a total amplitude of 1.5mm, the frequency being varied uniformly between the approximate limits of 10 and 55Hz. The frequency range, from 10 to 55Hz and return to 10Hz, shall be traversed in approximately 1 minute. This motion shall be applied for a period of 2 hours in each 3 mutually perpendicular directions (total of 6 hours)				ng varied 5Hz. The c, shall be ll be pendicular
	12 Deflection		No cracking or marking defects shall occur.			Solder the cap in Fig.2 using Then apply a f The soldering reflow method soldering is ur	pacitor to the te a eutectic sold force in the dire shall be done and shall be c biform and free	est jig (gla er. ection sho either with onducted of defect	own in Fig.3. h an iron or usi with care so th s such as beat	ds) shown ng the nat the shock	
12						Pressurize R230 Flexure : ≤1 (in mm)					
13	Solderabi Terminati	ility of on	75% of the terminations is to be soldered evenly and continuously.			Immerse the capacitor in a solution of ethanol (JIS-K-8101) and rosin (JIS-K-5902) (25% rosin in weight proportion). Preheat at 80 to 120°C for 10 to 30 seconds. After preheating, immerse in eutectic solder solution for 2±0.5 seconds at 230±5°C.					
		The measured and observed characteristics shall satisfy the specifications in the following table.			hall satisfy the						
		Appearance	No marking defects. Within ±2.5% or ±0.25pF (Whichever is larger)				Preheat the capacitor at 120 to 150°C for 1 minute.				
	Resistance	Capacitance Change									
14	to Soldering Heat	Q	30pF and over : Q 30pF and below : 0 C : Nominal Capac	≧1,000 Q≧400+20C citance (pF)			for 10 $\pm$ 0.5 seconds. Let sit at room temperature for 24 $\pm$ 2 h			nours.	210200
		I.R.	More than 10,000	MΩ or 500Ω • F	(Whichever	is smaller)					
		Dielectric Strength	No failure				_				
			The measured and observed characteristics shall satisfy the specifications in the following table.								
		Appearance	No marking defect	S.			Fix the capacitor to the supporting jig in the same manner and				
45	Temperature	Capacitance Change         Within ±2.5% or ±0.25pF (Whichever is larger)		according to the four heat treatments listed in the following table. Let sit for 24±2 hours at room temperature, then measure.							
15	Cycle	Q	30pF and over : Q 30pF and below : ( C : Nominal Capac	≧1,000 Q≧400+20C citance (pF)			Step Temp.(°C)	1 Min. Operating Temp3	2 Room Temp.	3 Max. Operating Temp. +3 -0	4 Room Temp.
		I.R.	More than 10.000	MΩ or 500Ω • F	(Whichever	is smaller)	Time(min.)	30±3	2 to 3	30±3	2 to 3
		Dielectric Strength	No failure							I	
			The measured and specifications in th	d observed char e following table	acteristics sl	hall satisfy the					
		Appearance	No marking defect	S.							
16	Humidity, Steady	Capacitance Change	Within ±5% or ±0. (Whichever is large	5pF er)			Sit the capacit hours.	or at 40±2℃ a	nd 90 to 9	95% humidity fo	or 500±12
10	State	Q	30pF and over. : C 10pF and over, 30 10pF and below : C C : Nominal Capac	2≧350 pF and below : Q≧200+10C citance (pF)	Q≧275+ <del>5</del>	С	Remove and le type) at room	et sit for 24±2 temperature, th	hours (te nen meas	mperature com ure.	pensating
		LR. More than 10.000MQ or 500Q • F (Whichever is smaller)			1						



### **Specifications and Test Methods**

#### Continued from the preceding page.

			Specification				
No.	lte	em	Temperature Compensating Type	Test Method			
			The measured and observed characteristics shall satisfy the specifications in the following table.				
17		Appearance	No marking defects.				
	I luna altere	Capacitance Change	Within $\pm 7.5\%$ or $\pm 0.75$ pF (Whichever is larger)	Apply the rated voltage at 40±2°C and 90 to 95% humidity for			
	Load	Q	30pF and over : Q≥200 30pF and below : Q≥100+ <sup>10</sup> / <sub>3</sub> C C : Nominal Capacitance (pF)	Remove and let sit for 24±2 hours at room temperature, then measure. The charge/discharge current is less than 50mA.			
		I.R.	More than 500M $\Omega$ or 25 $\Omega$ • F (Whichever is smaller)				
		Dielectric Strength	No failure				
		The measured and observed characteristics shall satisfy the specifications in the following table.					
		Appearance	No marking defects.				
	Ulab	Capacitance Change	Within ±3% or ±0.3pF (Whichever is larger)	Apply 200% of the rated voltage for $1000\pm12$ hours at the			
18	Hign Temperature Load	Q	30pF and over. : Q≥350 10pF and over, 30pF and below : Q≥275+ 5 C 10pF and below : Q≥200+10C C : Nominal Capacitance (pF)	The charge/discharge current is less than 50mA.			
		I.R.	More than 1,000M $\Omega$ or 50 $\Omega \bullet F$ (Whichever is smaller)				
		Dielectric Strength	No failure				
19	ESR		$\begin{array}{llllllllllllllllllllllllllllllllllll$	The ESR shall be measured at room Temp. and frequency 1±0.2GHz with the equivalent of BOONTON Model 34A.			
	Lon		10pF <c≦20pf 400mω="" :="" below<="" td=""><td>10pF<c≦20pf 400mω="" :="" below<="" td=""><td>The ESR shall be measured at room Temp. and frequency</td></c≦20pf></td></c≦20pf>		10pF <c≦20pf 400mω="" :="" below<="" td=""><td>The ESR shall be measured at room Temp. and frequency</td></c≦20pf>	The ESR shall be measured at room Temp. and frequency	

#### Table A

Char.	Tanan Oraff	Capacitance Change from 25°C Value (%)							
	Temp. Coeff. (ppm/℃) Note 1	—55℃		−30°C		−10°C			
		Max.	Min.	Max.	Min.	Max.	Min.		
C0G	0±30	0.58	-0.24	0.40	-0.17	0.25	-0.11		

Note 1 : Nominal values denote the temperature coefficient within a range of 25 to 125°C.(for C0∆)



#### **GRM Series Data**

#### ■ Capacitance-Temperature Characterstics



■ Capcitance-AC Voltage Characteristics



#### ■ Impedance-Frequency Characteristics



#### ■ Capcitance-DC Voltage Characteristics



■ Capacitance Change-Aging



■ Allowable Voltage-Frequency



Continued on the following page.



### **GRM Series Data**

Continued from the preceding page.

#### ■ Allowable Current-Frequency



#### ■ Allowable Appearant Power



